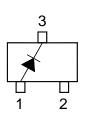
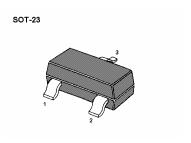
### SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification

#### **Features**

- Small surface mounting type.
- High reliability.





SOT-23 Plastic Package

### Marking

Marking Code: FF

# Absolute Maximum Ratings (T<sub>a</sub>= 25°C)

Parameter	Symbol	Value	Unit	
Maximum Peak Reverse Voltage	$V_{RM}$	40	٧	
DC Reverse Voltage	V <sub>R</sub>	40	V	
Mean Rectifying Current	Io	0.1	А	
Peak Forward Surge Current 1)	I <sub>FSM</sub>	1	А	
Junction Temperature	T <sub>j</sub>	125	°C	
Storage Temperature Range	T <sub>s</sub>	-40 to +125	°C	

 $<sup>^{1)}</sup>$  60Hz for 1  $\bigcirc$ 

## Characteristics at T<sub>a</sub> = 25 °C

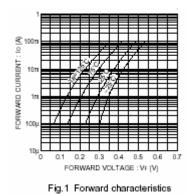
Parameter	Symbol	Min	Тур	Max	Unit
Forward Voltage	\/			0.45	V
at I <sub>F</sub> = 10mA	V <sub>F</sub>	-	-	0.45	V
Reverse Current	I <sub>R</sub>	-	-	1	μA
at V <sub>R</sub> =10V					
Capacitance Between Terminals	Ст	-	6	-	pF
at V <sub>R</sub> =10V, f=1MHz					

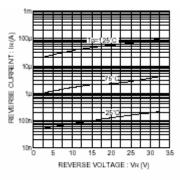






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CAPACITANCEBETWEEN REVERSE VOLTAGE: VR (V)

Fig.2 Reverse characteristics

Fig.3 Capacitance between terminals characteristics

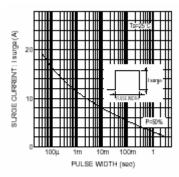


Fig.4 Surge current characteristics

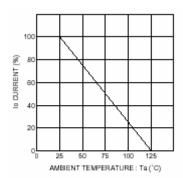


Fig.5 Denating curve (mounting on glass epoxy PCBs)











